

# RF Power MOSFET Transistor 15 W, 2 - 175 MHz, 12 V

#### Features

- N-Channel enhancement mode device
- DMOS structure
- Lower capacitances for broadband operation
- High saturated output power
- Lower noise figure than bipolar devices
- Specifically designed for 12 volt applications
- RoHS Compliant

#### ABSOLUTE MAXIMUM RATINGS AT 25° C

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V <sub>DS</sub>	40	V
Gate-Source Voltage	$V_{GS}$	20	V
Drain-Source Current	I <sub>DS</sub>	4	А
Power Dissipation	PD	87.5	W
Junction Temperature	TJ	200	°C
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C
Thermal Resistance	$\theta_{\text{JC}}$	2	°C/W

## **TYPICAL DEVICE IMPEDANCE**

F (MHz)	Z <sub>IN</sub> (Ω)	Z <sub>LOAD</sub> (Ω)			
30	3.0 - j25	4.0 - j3.0			
100	3.0 - j15	3.5 - j1.5			
175	5.0 - j8	4.0 - j0.0			
V <sub>DD</sub> = 12V, I <sub>DQ</sub> = 100mA, P <sub>OUT</sub> = 15W					

 $Z_{\mbox{\scriptsize IN}}$  is the series equivalent input impedance of the device from gate to source.

 $Z_{\mbox{\scriptsize LOAD}}$  is the optimum series equivalent load impedance as measured from drain to ground.

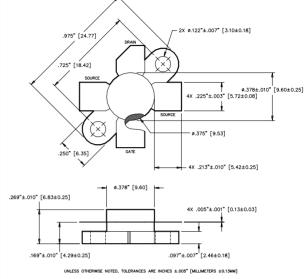
# ELECTRICAL CHARACTERISTICS AT 25°C

Parameter	Symbol	Min	Max	Units	Test Conditions
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	-	V	$V_{GS} = 0.0 \text{ V}$ , $I_{DS} = 5.0 \text{ mA}$
Drain-Source Leakage Current	I <sub>DSS</sub>	-	1.0	mA	$V_{GS}$ = 15.0 V , $V_{GS}$ = 0.0 V
Gate-Source Leakage Current	I <sub>GSS</sub>	-	1.0	μA	$V_{GS}$ = 20.0 V , $V_{DS}$ = 0.0 V
Gate Threshold Voltage	V <sub>GS(TH)</sub>	20	6.0	V	V <sub>DS</sub> = 10.0 V , I <sub>DS</sub> = 100 mA
Forward Transconductance	G <sub>M</sub>	0.5	-	S	$V_{\text{DS}}$ = 10.0 V , $I_{\text{DS}}$ = 1000 mA , $\Delta$ $V_{\text{GS}}$ = 1.0 V
Input Capacitance	CISS	-	50	pF	V <sub>DS</sub> = 12.0 V , F = 1.0 MHz
Output Capacitance	C <sub>OSS</sub>	-	60	pF	V <sub>DS</sub> = 12.0 V , F = 1.0 MHz
Reverse Capacitance	C <sub>RSS</sub>	-	12	pF	V <sub>DS</sub> = 12.0 V , F = 1.0 MHz
Power Gain	G <sub>P</sub>	9.5	-	dB	$V_{DD}$ = 12.0 V, $I_{DQ}$ = 100 mA, $P_{OUT}$ = 15 W F =175 MHz
Drain Efficiency	ŋ₀	60	-	%	$V_{DD}$ = 12.0 V, $I_{DQ}$ = 100 mA, $P_{OUT}$ = 15 W F =175 MHz
Load Mismatch	VSWR-T	-	30:1	-	$V_{DD}$ = 12.0 V, $I_{DQ}$ = 100 mA, $P_{OUT}$ = 15 W F =175 MHz

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# Package Outline



LETTER	MILLIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
А	24.64	24.89	.970	.980	
В	18.29	18.54	.720	.730	
С	20.07	20.83	.790	.820	
D	9.47	9.73	.373	.383	
E	6.22	6.48	.245	.255	
F	5.64	5.79	.222	.228	
G	2.92	3.30	.115	.130	
н	2.29	2.67	.090	.105	
J	4.04	4.55	.159	.179	
К	6.58	7.39	.259	.291	
L	.10	.15	.004	.006	

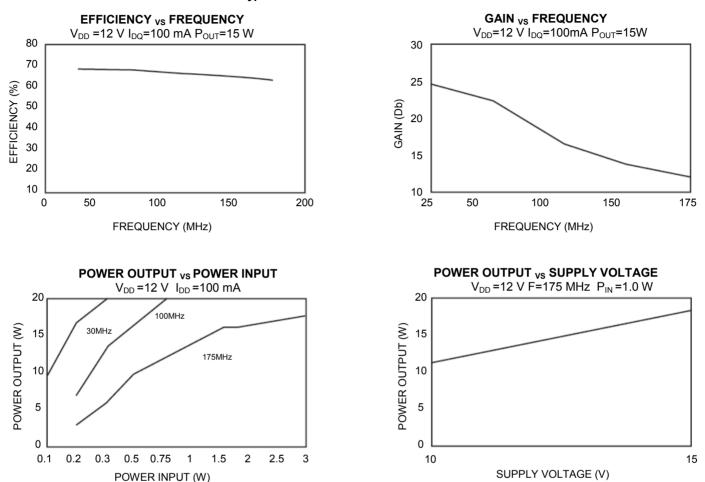
Rev. V1





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Rev. V1



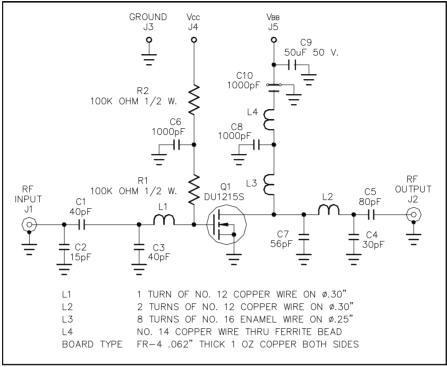
**Typical Broadband Performance Curves** 

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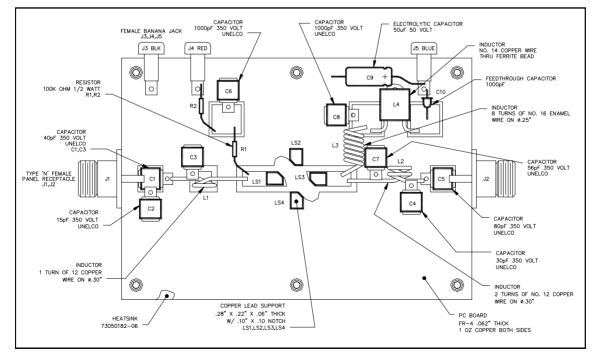
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## **TEST FIXTURE SCHEMATIC**



#### **TEST FIXTURE ASSEMBLY**





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Rev. V1

# DU1215S

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Rev. V1

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